

MJE5852

HIGH VOLTAGE PNP POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- PNP TRANSISTOR
- HIGH VOLTAGE CAPABILITY

APPLICATIONS:

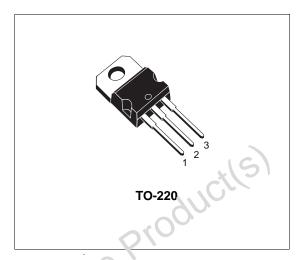
- SWITCHING REGULATORS
- MOTOR CONTROL
- INVERTERS

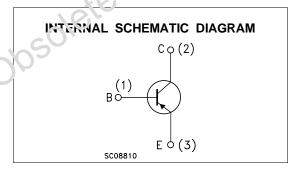
DESCRIPTION

The MJE5852 is manufactured using High Voltage PNP Multi-Epitaxial technology for high switching speed and high voltage capability.

It is intended for use in high frequency and efficiency converters, switching regulators and motor control.

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ABSOLUTE MAJIMUM RATINGS

Symbol	Parameter	Value	Unit V V	
VICES	Collector-Emitter Voltage (V _{BE} = 0)	-450		
CEO	Collector-Emitter Voltage (I _B = 0)	-400		
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	-7	V	
lc	Collector Current	-8	A A A	
I _{CM}	Collector Peak Current (t _p < 5ms)	-16		
IB	Base Current	-4		
I _{BM}	Base Peak Current (t _p < 5ms)	-8	А	
P _{tot}	Total Dissipation at $T_c \le 25 \ ^{\circ}C$	80	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

September 2003

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

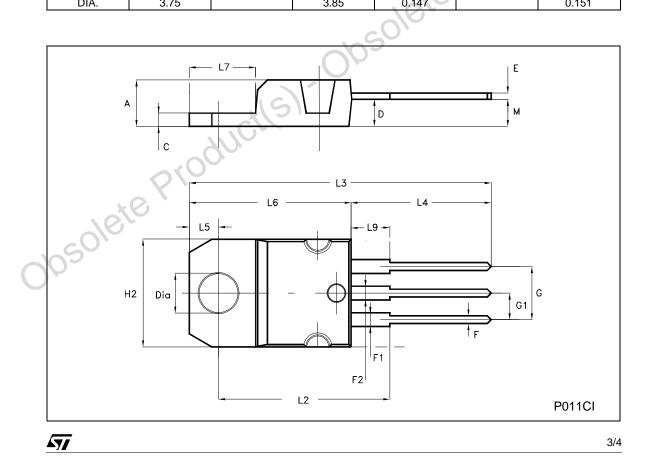
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = -450 V			-500	μA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = -6 V$			-1	mA
VCEO(sus)*	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = -10 mA	-400			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage				-2 -5	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	$I_{\rm C} = -4 \text{ A} \qquad I_{\rm B} = -1 \text{ A}$			-1.5	SY
h _{FE} *	DC Current Gain	I _C = -2 A V _{CE} = -5 V I _C = -5 A V _{CE} = -5 V	15 5	1	CI	
t _s	RESISTIVE LOAD Storage Time	$I_{\rm C} = -4 \ {\sf A}$ $V_{\rm CC} = -250 \ {\sf V}$	v	00.	2 0.5	μs μs
t _f Pulsed: Pulse for PNP type v	Fall Time e duration = 300 µs, duty cycle 1 voltage and current values are ne	$I_{B1} = -I_{B2} = -1 \text{ A}$ $t_p = 40 \ \mu\text{s}$.5 % egative.	ster		0.3	μο
tr Pulsed: Pulse or PNP type v	Fall Time e duration = 300 µs, duty cycle 1 voltage and current values are ne	$\begin{array}{c} I_{B1} = -I_{B2} = -1 \text{ A} \\ \text{ t}_{p} = 40 \mu\text{s} \\ \text{ egative.} \end{array}$	ete r	1	0.5	μο
tr Pulsed: Pulse or PNP type v	Fall Time e duration = 300 µs, duty cycle 1 voltage and current values are ne	$I_{B1} = -I_{B2} = -1 A$ $I_p = 40 \ \mu s$ egative.	ete r		0.5	μο

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DIM.	mm		inch			
Divi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	IC
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600	Z	0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	





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